

Yuichi Kawamura

List of Publications by Year in descending order

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10
papers

44
citations

1684188

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1720034

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docs citations

10
times ranked

35
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical properties of InAsSbN single quantum wells grown on InP substrates for 2-1¼m-wavelength region. Journal of Crystal Growth, 2013, 378, 69-72.	1.5	8
2	2.86 Åm room-temperature light emission of InGaAsN/GaAsSb type-II quantum well diodes grown on InP substrates. Japanese Journal of Applied Physics, 2014, 53, 028004.	1.5	8
3	Infrared defect dynamics“Nitrogen-vacancy complexes in float zone grown silicon introduced by electron irradiation. Journal of Applied Physics, 2018, 123, .	2.5	7
4	InAsSbN Quantum Well Laser Diodes Operating at 2-Åm-Wavelength Region Grown on InP Substrates. Japanese Journal of Applied Physics, 2005, 44, L1112-L1114.	1.5	5
5	Effective mass of two-dimensional electrons in InGaAsN/GaAsSb type II quantum well by Shubnikov-de Haas oscillations. Journal of Applied Physics, 2016, 120, 142109.	2.5	5
6	Infrared defect dynamics - radiation induced complexes in silicon crystals grown by various techniques. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 833-841.	0.8	4
7	Infrared measurement and irradiation of ultra low carbon concentration silicon crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1931-1936.	0.8	3
8	Behavior of nitrogen in Si crystal during irradiation and post-annealing. , 2014, , .		3
9	Infrared defect dynamics: He irradiation induced complexes in high“quality silicon crystal. Physica Status Solidi (B): Basic Research, 2014, 251, 2205-2210.	1.5	1
10	Annealing effect on effective mass of two-dimensional electrons in InGaAsN/GaAsSb type II quantum well. Journal of Physics: Conference Series, 2018, 969, 012151.	0.4	0